



Kinetic Inductance Traveling Wave Parametric Amplifiers

[KTPAs or K-TWPAs or KTs]

Corwin Shiu

BREAD collaboration meeting 01/14/2026



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Doug Bennett

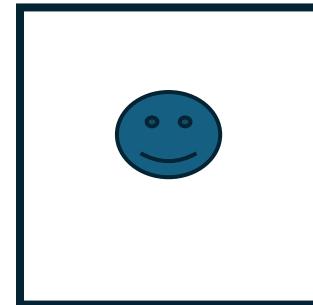
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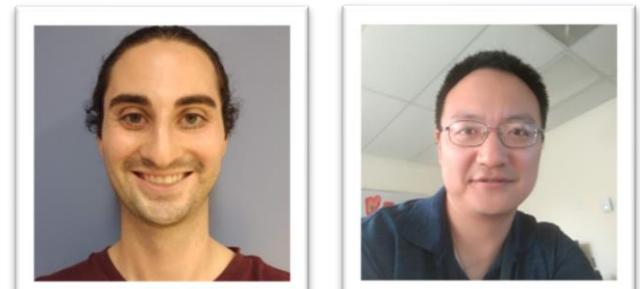
Jordan Wheeler

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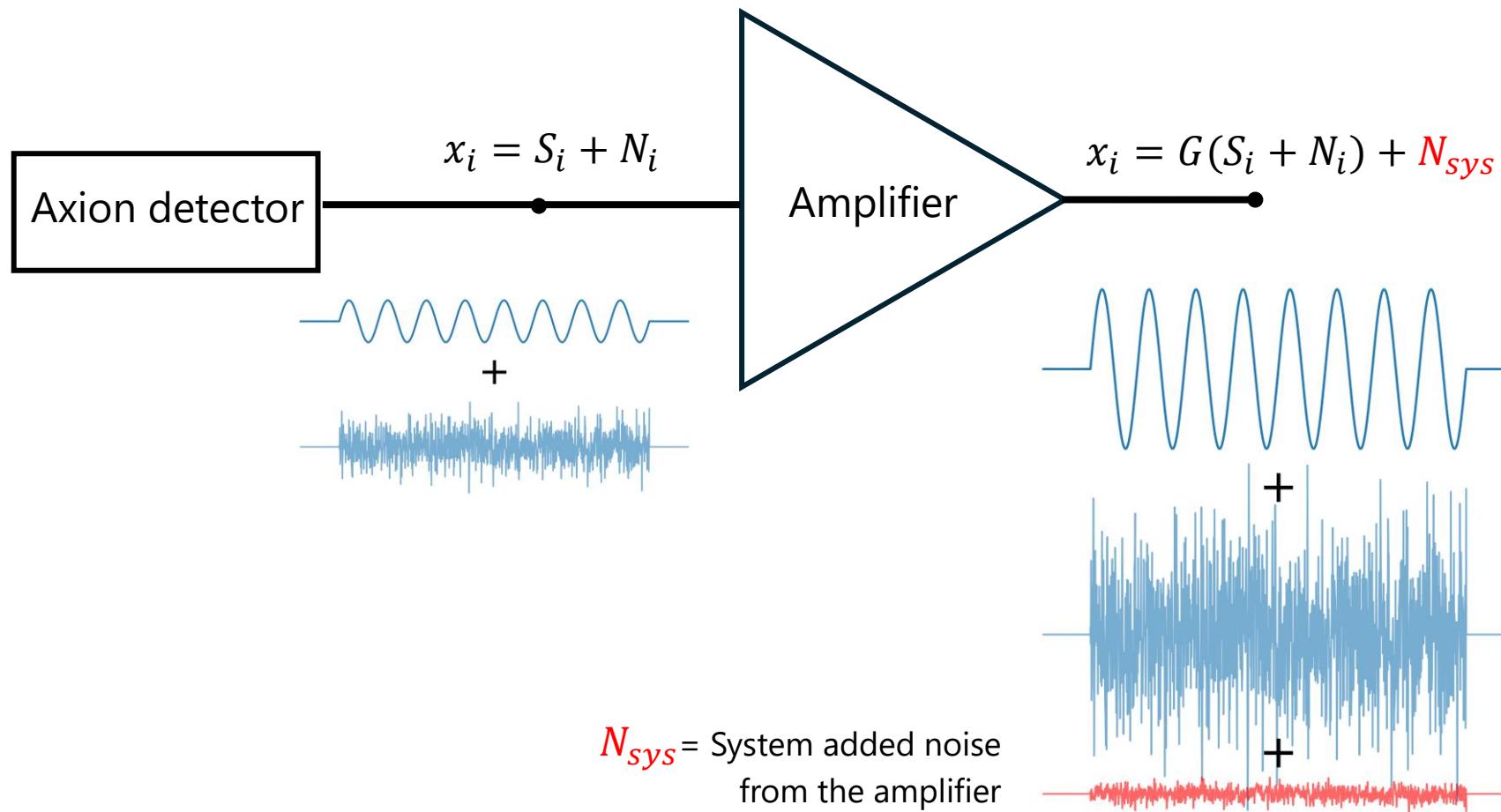


Andrea Giachero
Pietro Campana



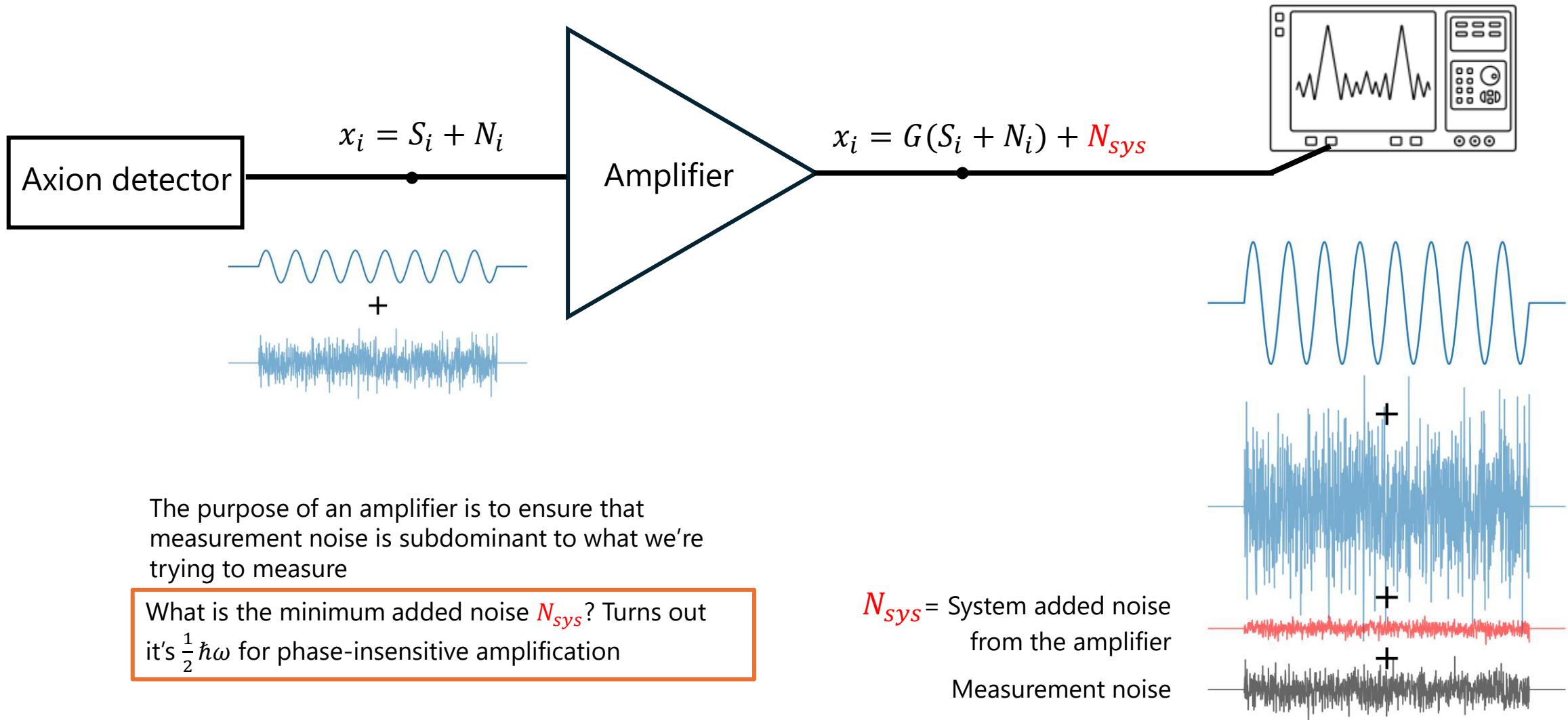
Logan Howe
Jiansong Gao

What is an amplifier?



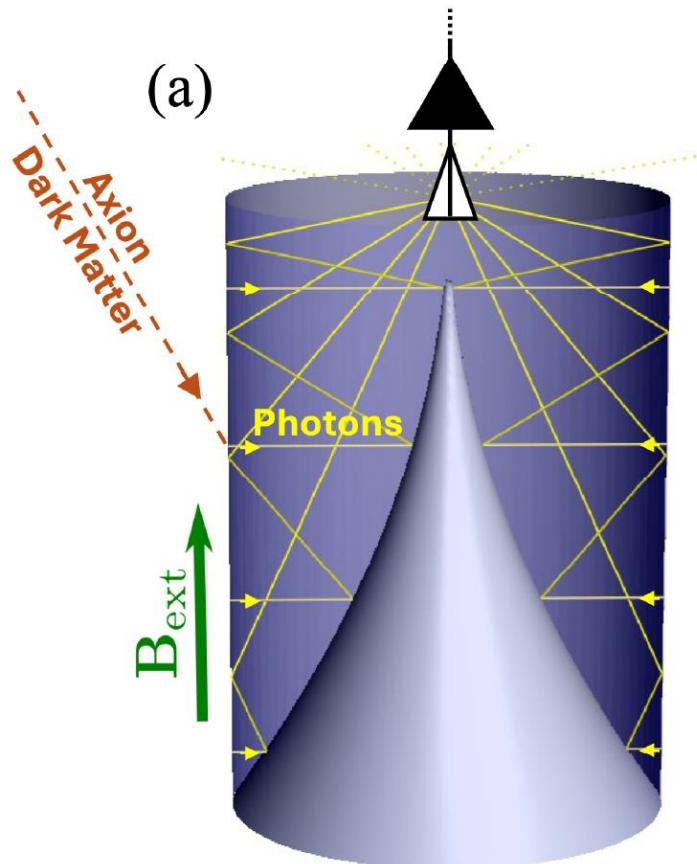
Amplification will always decrease the signal-to-noise ratio

What is an amplifier?

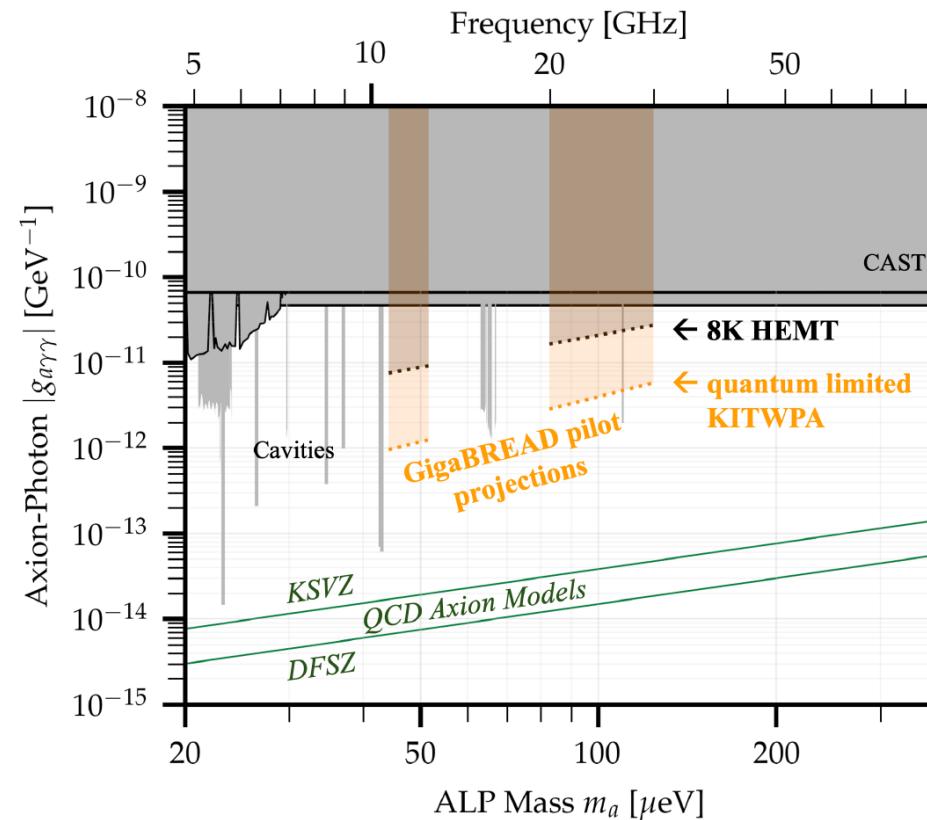


Using quantum-limited amplifiers for axion searches

Figures from the DOE Quantized proposal



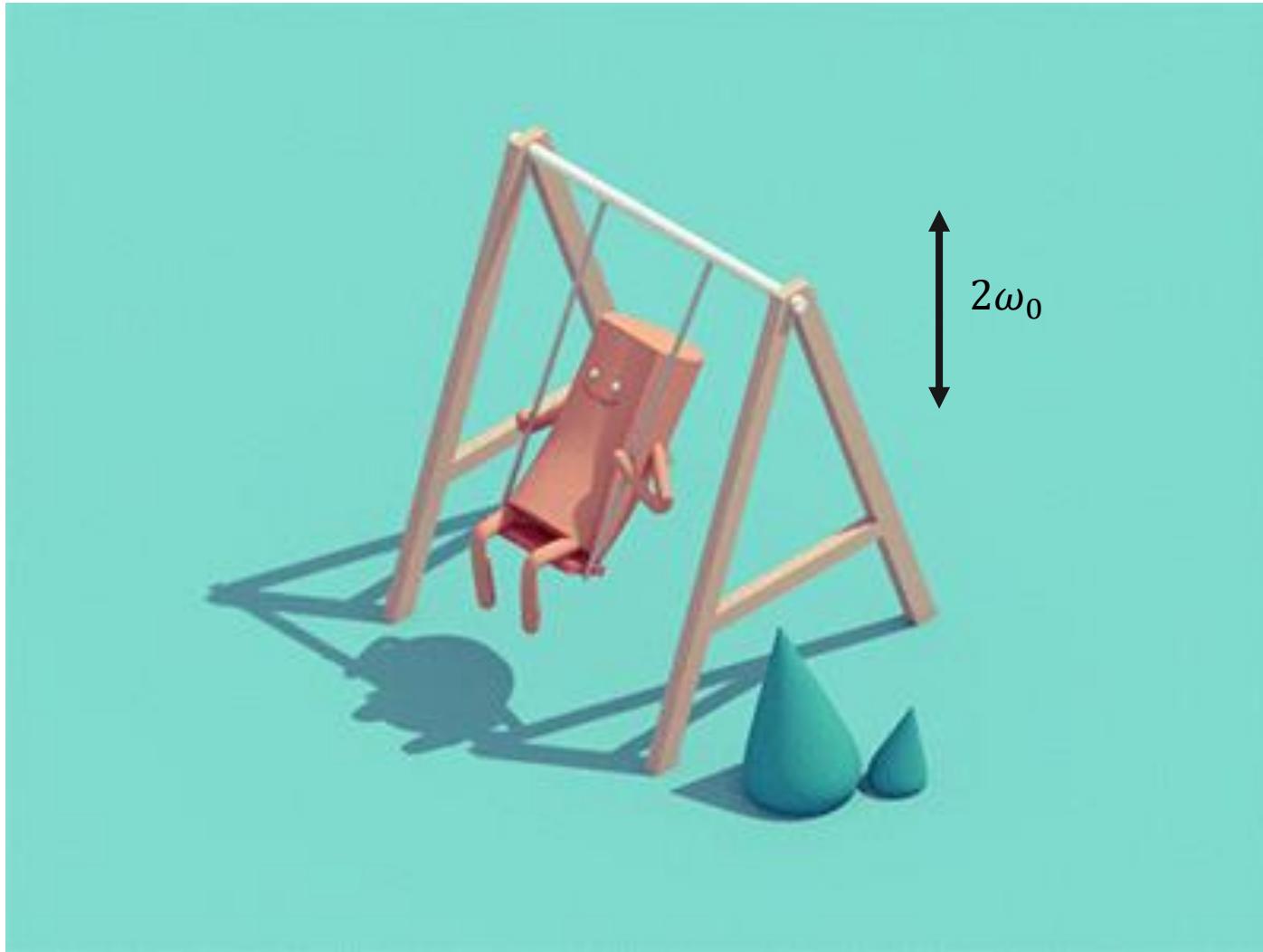
GigaBREAD concept



Motivated to use KTWPAs

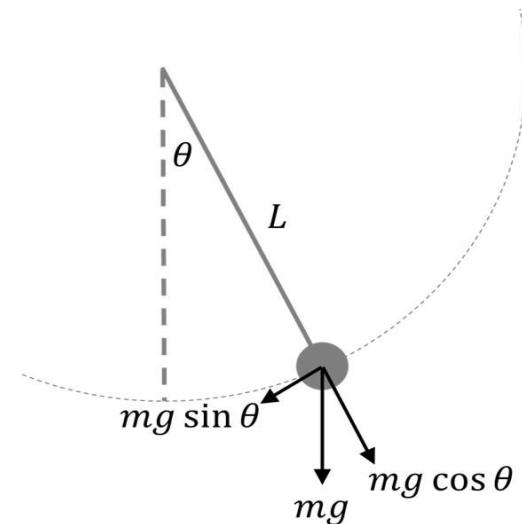
- Broadband gain to match the frequency band of GigaBREAD
- Near-quantum limited noise performance
- Insensitive to magnetic fields

An example of a mechanical parametric oscillator



Two ingredients make this possible:

- Modulation: Center of mass-oscillations occur at twice the frequency of the pendulum
- Nonlinearity: The restoring force of the pendulum is *nonlinear*: $\ddot{x} \sim -\sin \theta$

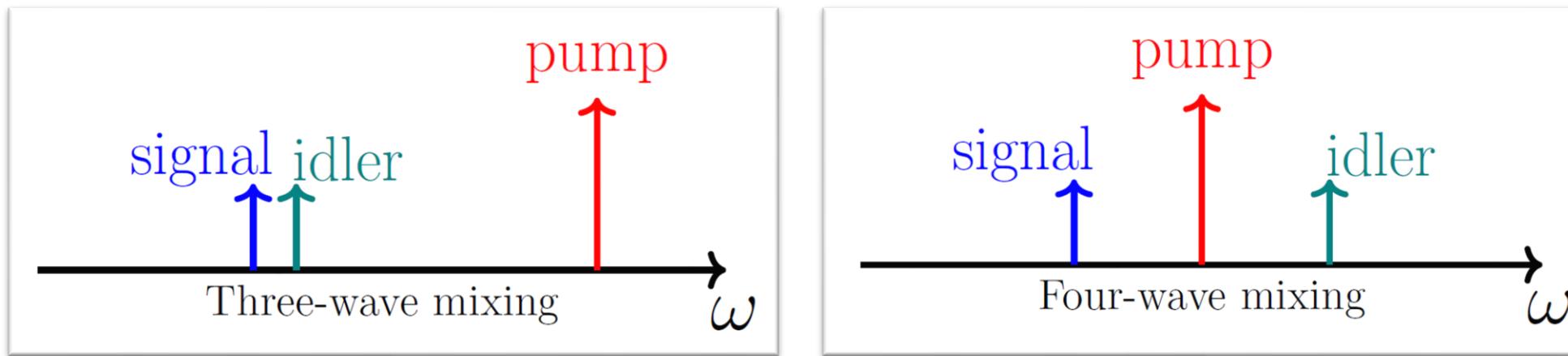


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Kinetic Inductance Traveling Wave Parametric Amplifier

- A *non-linear* transmission line allows for energy conversion if we apply a pump tone (creating modulation).
 - Three-wave mixing: $\omega_p = \omega_s + \omega_i$
 - Four-wave mixing: $2\omega_p = \omega_s + \omega_i$

ω_p = pump photon
 ω_s = signal photon
 ω_i = idler photon



- Non-linear transmission line can be created with kinetic inductance or Josephson Junctions (subject of next talk)

Kinetic Inductance Traveling Wave Parametric Amplifier

- Kinetic inductance (in the thin-film limit):

$$L_s = \frac{\hbar R_s}{\pi \Delta_0} = \frac{\hbar \rho_n}{\pi \Delta_0 t}$$

Normal state bulk resistance
Film thickness
Energy gap

- Typical kinetic inductance values for thin films:

- Nb ~ [0.1 – 1]pH/sq
- Al ~ [1 - 3]pH/sq
- **NbTiN ~ 30pH/sq** at 10nm

- Kinetic inductance is the inertial mass of the Cooper pairs is highly non-linear and parametrized by I^* , which sets the current scale in our device

$$L_k(I) = L_k(0) \left(1 + \frac{I^2}{I_*^2} + \dots \right)$$

- Kinetic inductance, in principle, is insensitive to magnetic fields so it is well suited for amplifiers in the B-field environment of an Axion experiment

Kinetic Inductance Traveling Wave Parametric Amplifier

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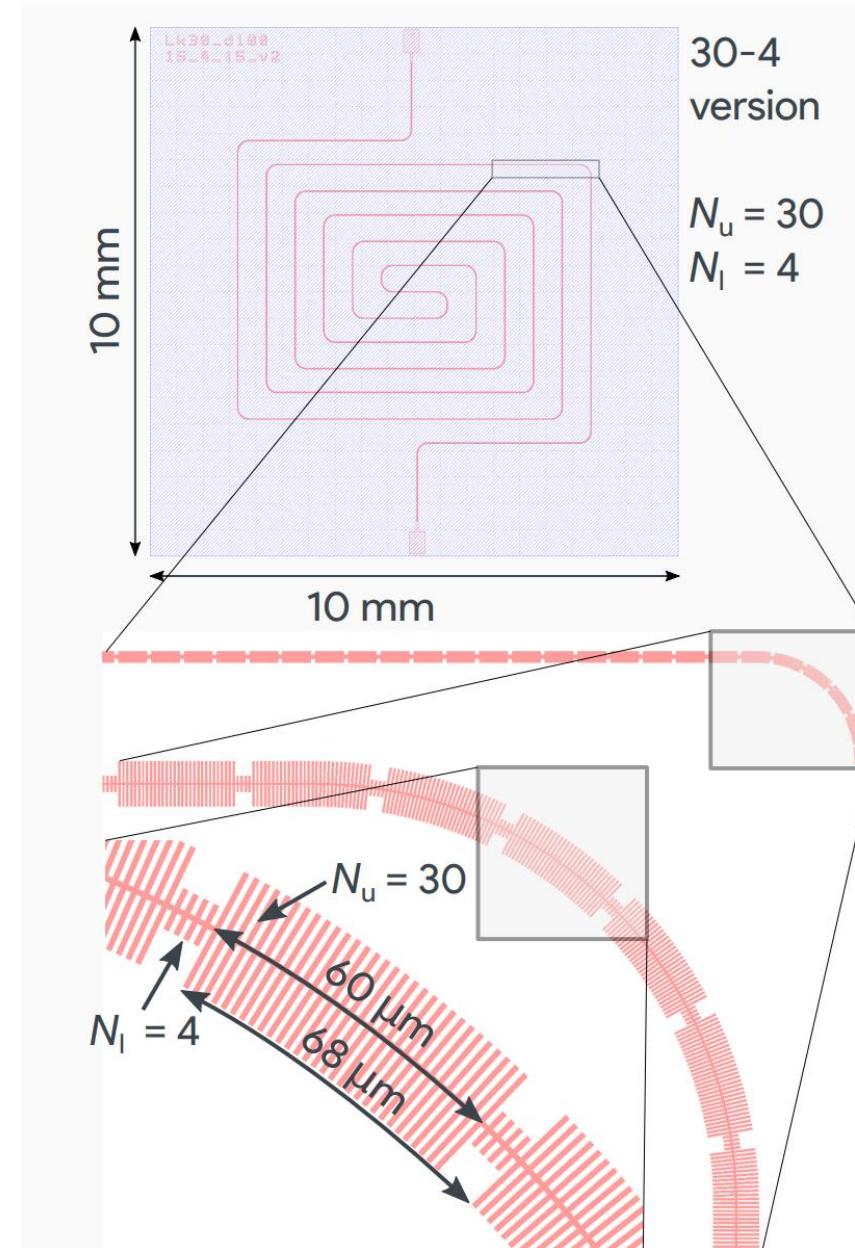
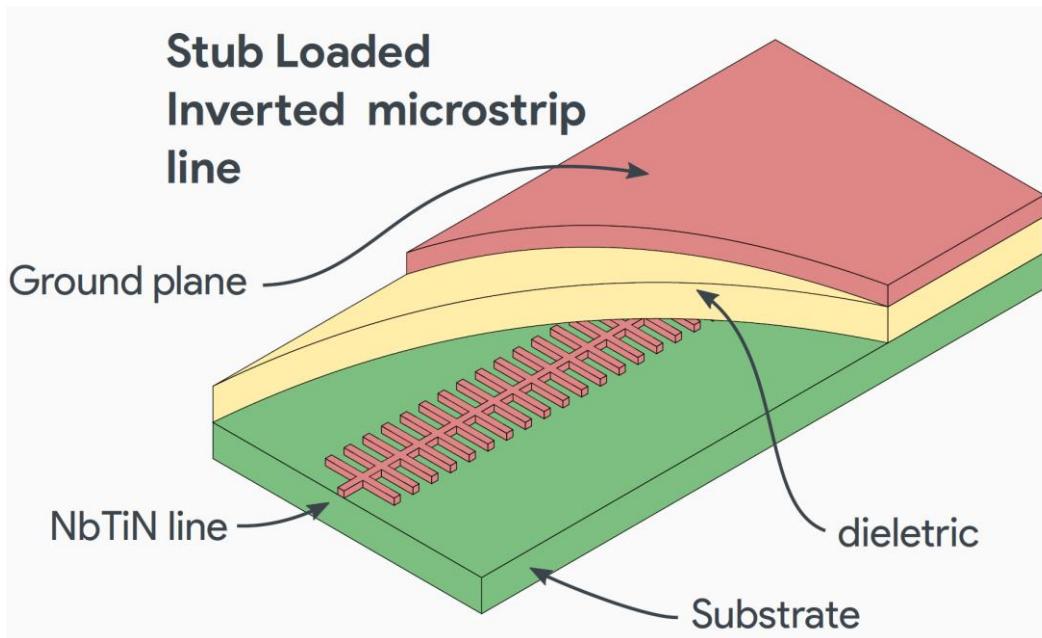
$$L_k(I) = L_k(0) \left(1 + \frac{I^2}{I_*^2} + \dots \right)$$

- Kinetic inductance, in principle, is insensitive to magnetic fields and can operate in strong B-field environment such as an Axion experiment

General overview

- 10nm NbTiN $L_k = 30\text{pH/sq}$
- Low-loss 150nm a-Si
- 40,000 unit cells for 8cm physical length
- Minimum feature size = 3μm
- $I^* \sim 2 - 3\text{mA}$
- Compression point: -70dBm

Broadband phase-matching via dispersion engineering



The need for dispersion engineering

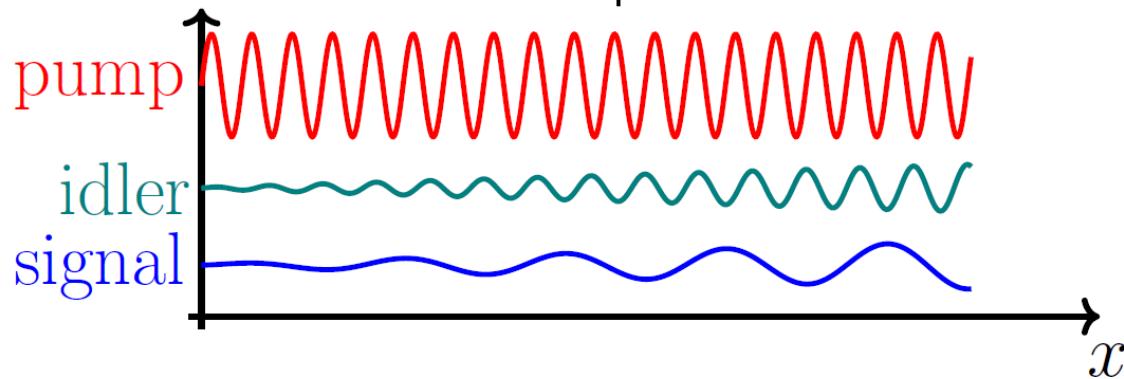
- If you follow the coupled mode equations, the phase matching condition:

The 4-wave mixing amplitude:

$$\Delta_k = k_p - k_s - k_i = -\frac{\xi I_{p0}^2}{8} (k_p - 2k_s - 2k_i)$$

$$\xi = \left(\frac{1}{I_*^2 + I_{dc}^2} \right)$$

Position down the TWPA when phased matched



Phase matching makes sure that the pump keeps pushing on the signal as it propagates down the line, instead of sometimes pushing, sometimes pulling

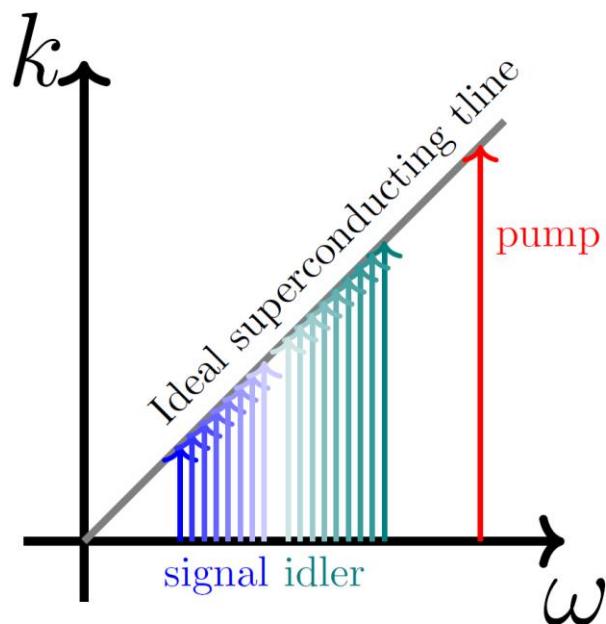
The need for dispersion engineering

- If you follow the coupled mode equations, the phase matching condition:

The 4-wave mixing amplitude:

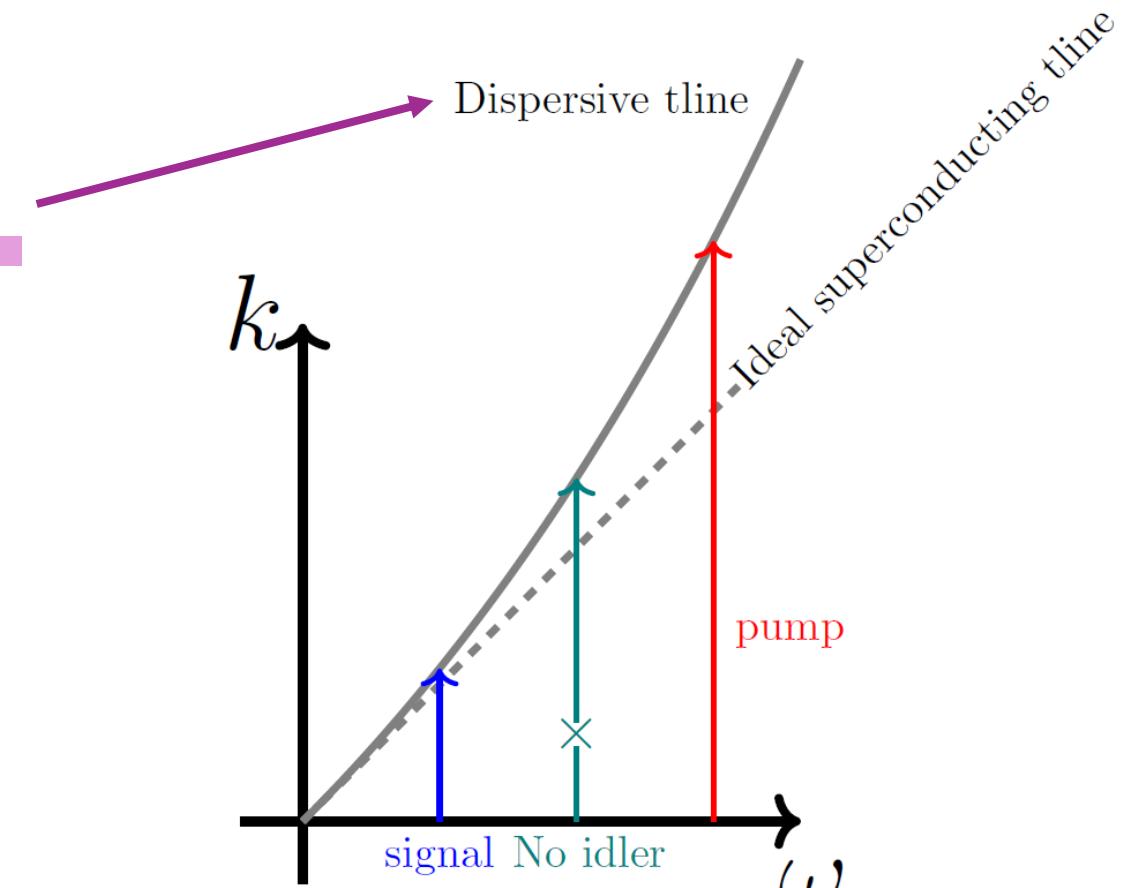
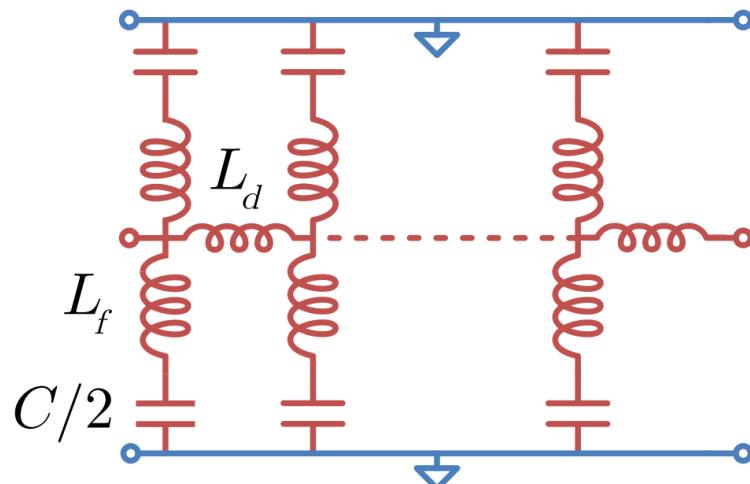
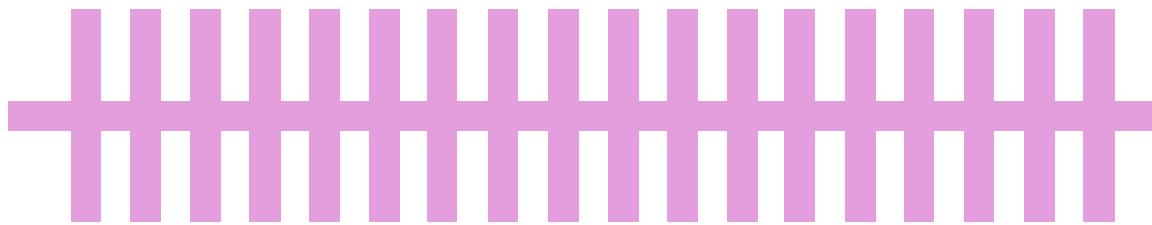
$$\Delta_k = k_p - k_s - k_i = -\frac{\xi I_{p0}^2}{8} (k_p - 2k_s - 2k_i) \quad \xi = \left(\frac{1}{I_*^2 + I_{dc}^2} \right)$$

- In the limit that the four-wave mixing is small ($I_{p0} \ll I_*, I_{dc}$), then $\Delta_k = 0$.
- A regular superconducting transmission line will naturally fulfill this condition, achieving 3WM:



However, this is undesirable because this line would support all sorts of parametric conversion processes at once, increasing noise and reducing our gain.

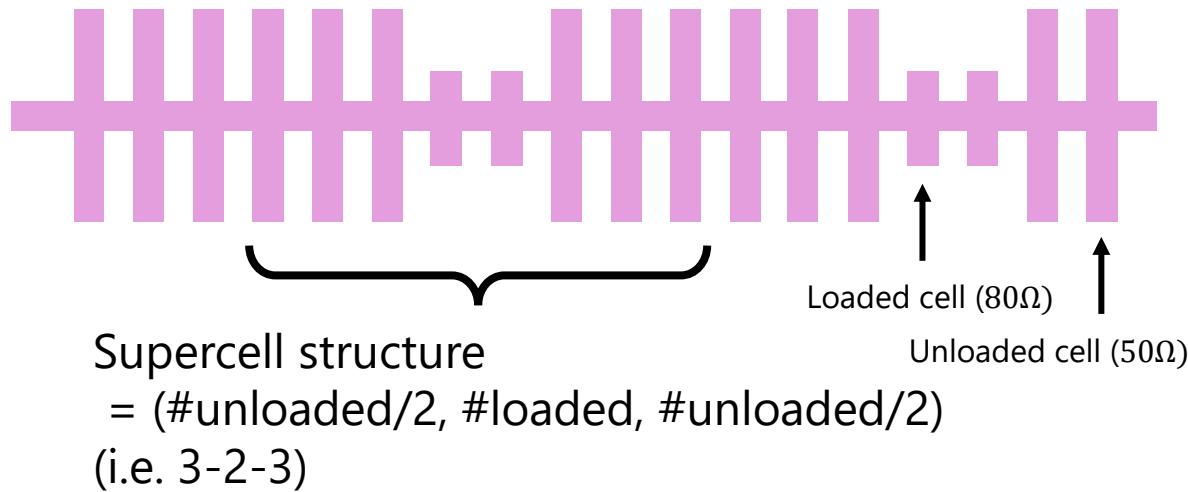
Our approach to dispersion engineering



Can't satisfy both energy conservation
($\omega_p = \omega_s + \omega_i$) and the phase-matching condition

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Our approach to dispersion engineering

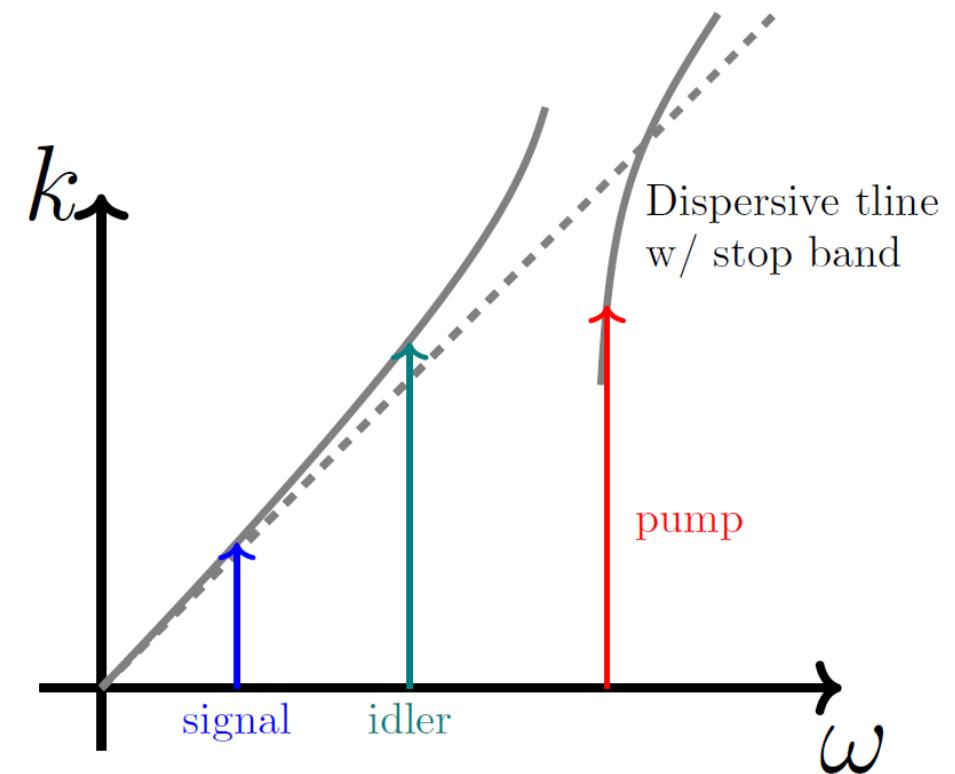


We engineer a stop band by modulating the impedance:

- Creates a resonance in the phase response
- Creates a "photonic" stopband in the amplitude response

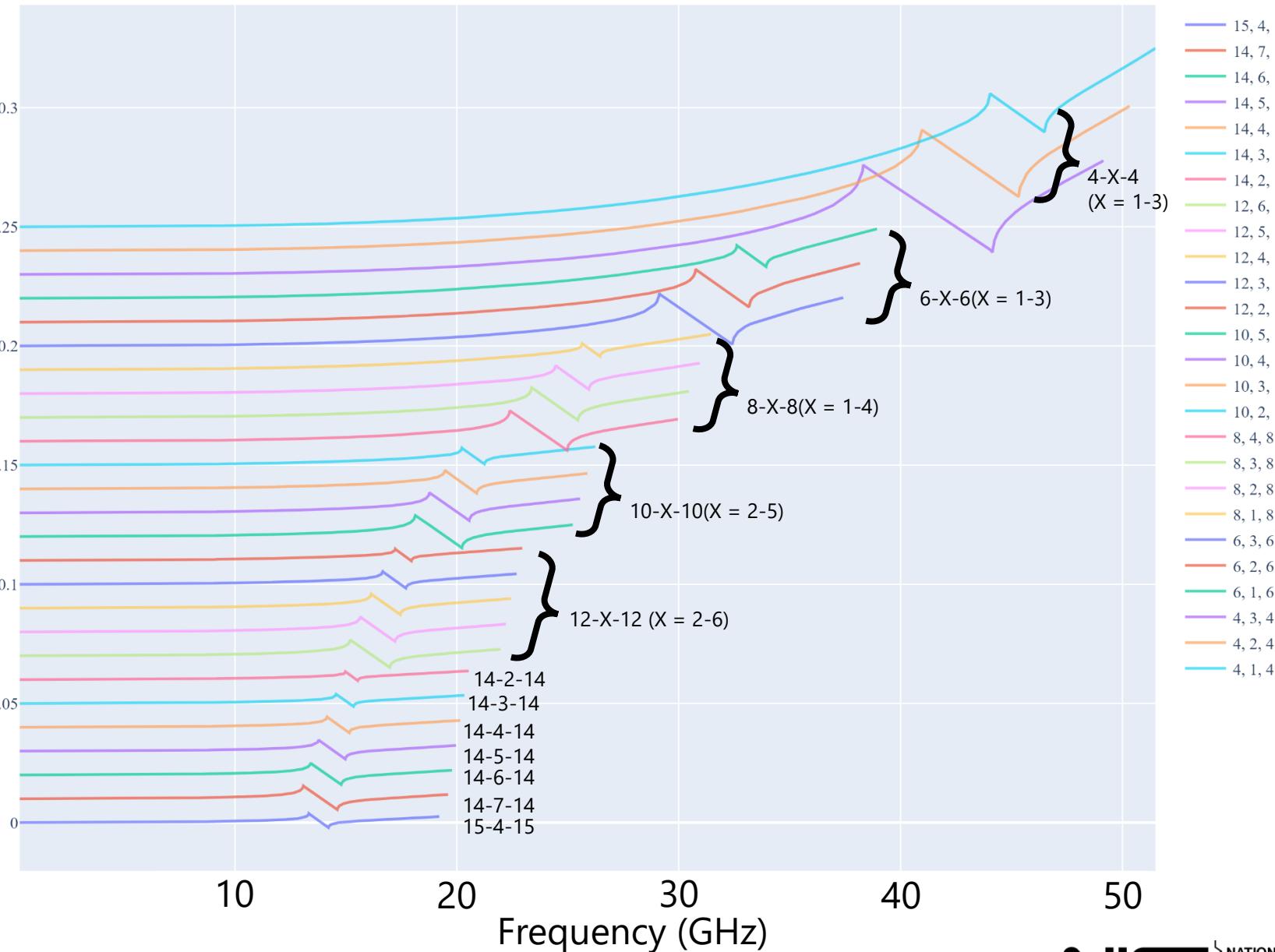
Allows us to find triplets $(k_p, k_s, k_i), (\omega_p, \omega_s, \omega_i)$ that satisfy

- [1] 3WM energy conservation
- [2] Phase-match condition

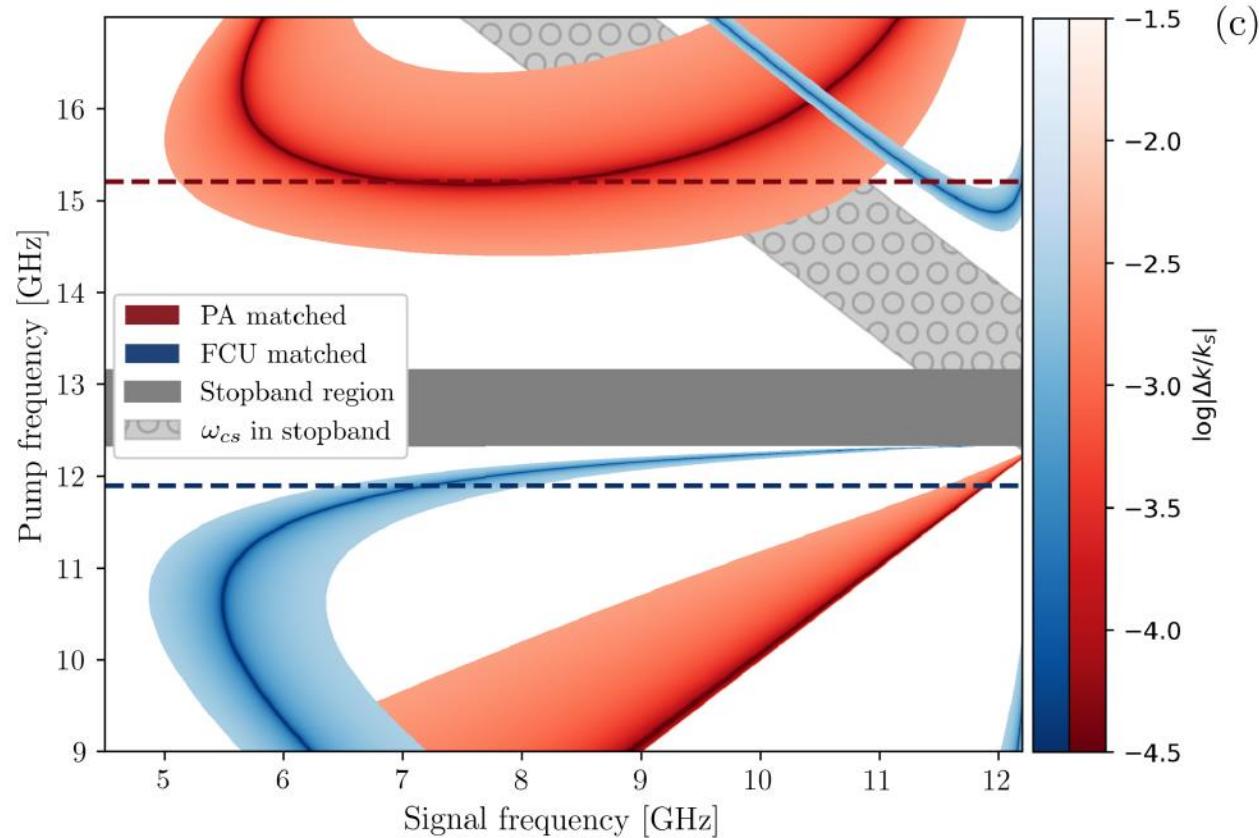


The supercell electrical length sets the stopband

Nonlinear
wavenumber k^*



When everything works well

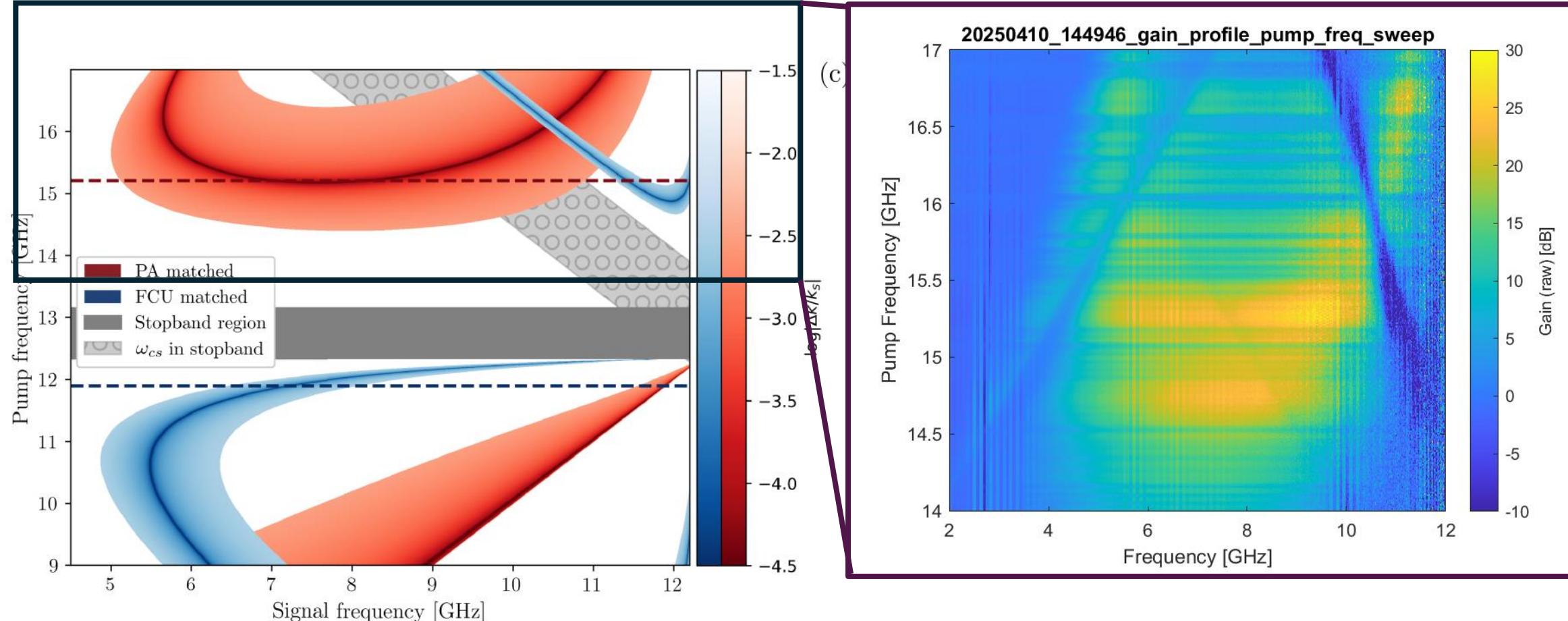


Colorscale is the error in phase matching (logged)

- PA = parametric amplification
- FCU = frequency up-conversion

Pietro Campana, publication under review:
Strongly Directional Amplification with a Kinetic Inductance Traveling Wave Parametric Amplifier

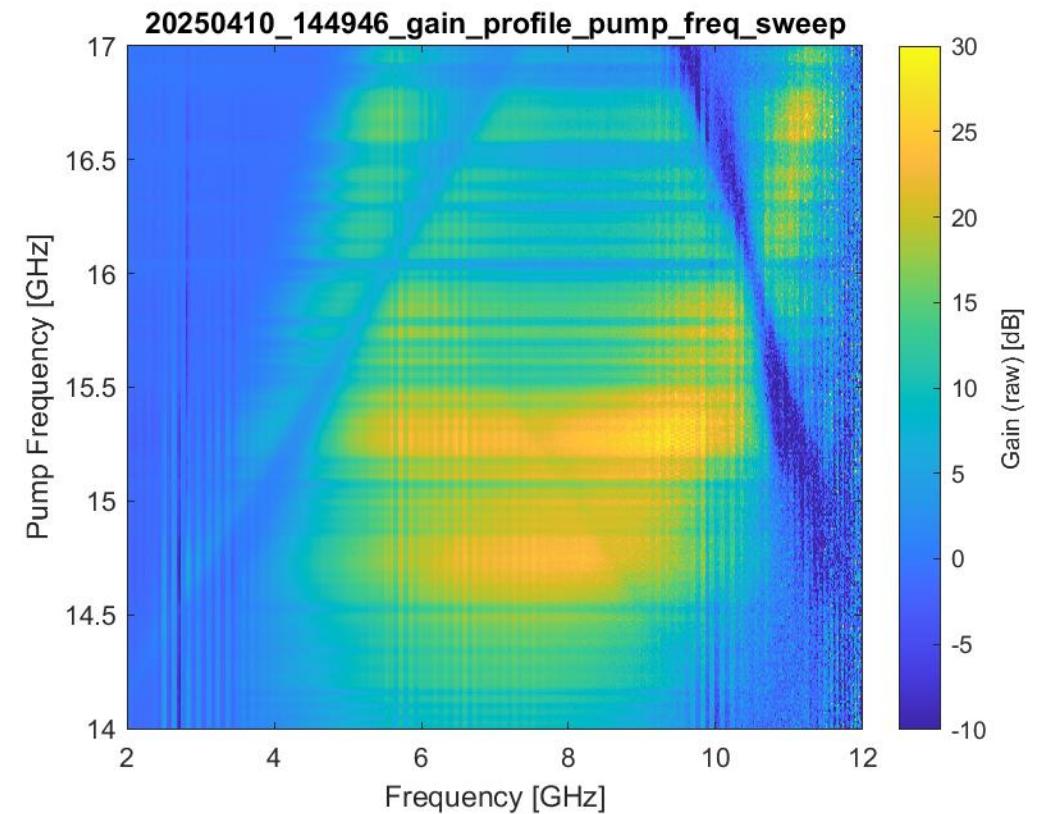
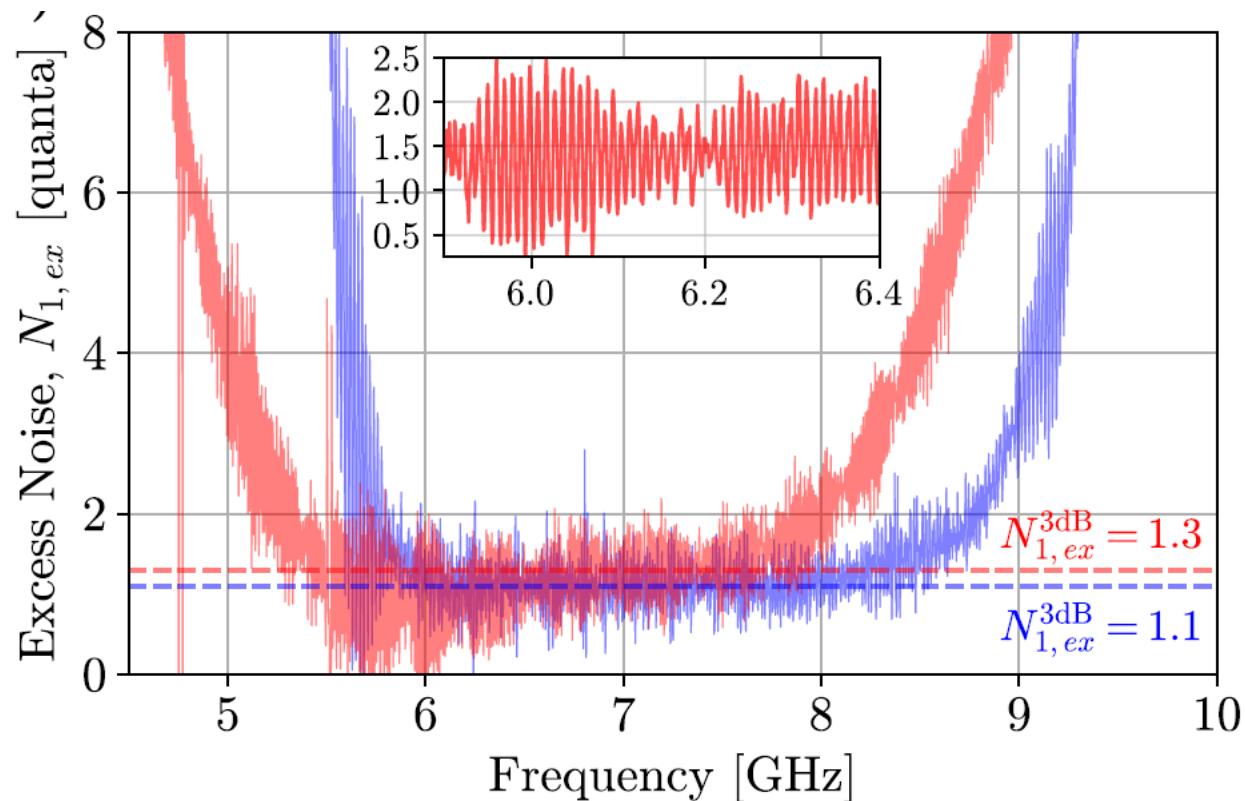
When everything works well



Pietro Campana, publication under review:
Strongly Directional Amplification with a Kinetic Inductance Traveling Wave Parametric Amplifier

Strong phase matching,
• Characteristic U shape
• Frequency conversion visible by eye

When everything works well



~1 quanta in excess of the quantum limit $\left(\frac{1}{2}\hbar\omega\right)$

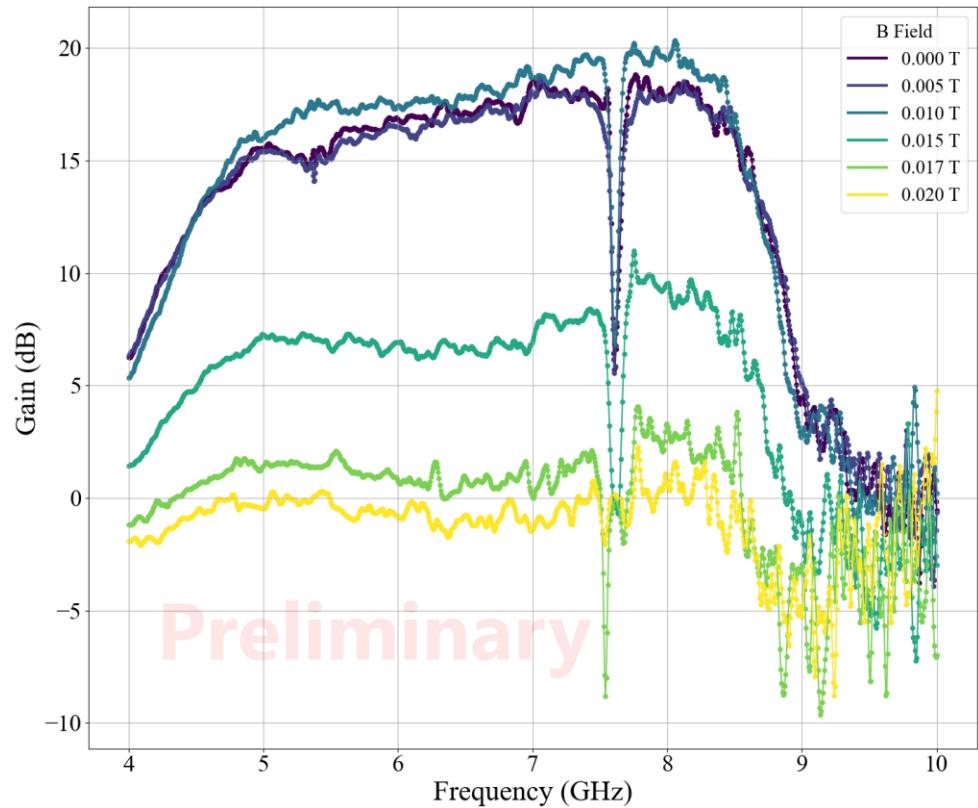
Howe, et. al. Near-quantum-limited Kinetic Inductance Traveling Wave Parametric Amplifiers: Methodology and Characterization

Direction of the research moving with an eye for higher frequencies

- Improvements in simulations
 - Extended coupled mode equations [Pietro: [twpasolver](#)]
- Improvements in dispersion engineering
 - Aluminum tips on capacitive fingers [Andrea]
 - Next-gen modulation techniques [Pietro,Andrea]
- Ultra-high kinetic inductance designs of 100pH/sq
 - Reduces the necessary pump powers [Andrea, see upcoming APS march meeting]
- Microwave packaging [Logan]
- On-chip integration of microwave components
 - Integrated bias-tees, directional couplers, diplexers [Logan, Corwin]
- Improvements in noise metrology [Corwin, see upcoming APS march meeting]
- Squeezed states in a KTWPA [Logan, paper under review]
- Magnetic field capability [Christian]
- Double KTWPA to replace the HEMT for potential space applications [Logan, Corwin]

Magnetic field compatibility [Christian Boutan at PNNL]

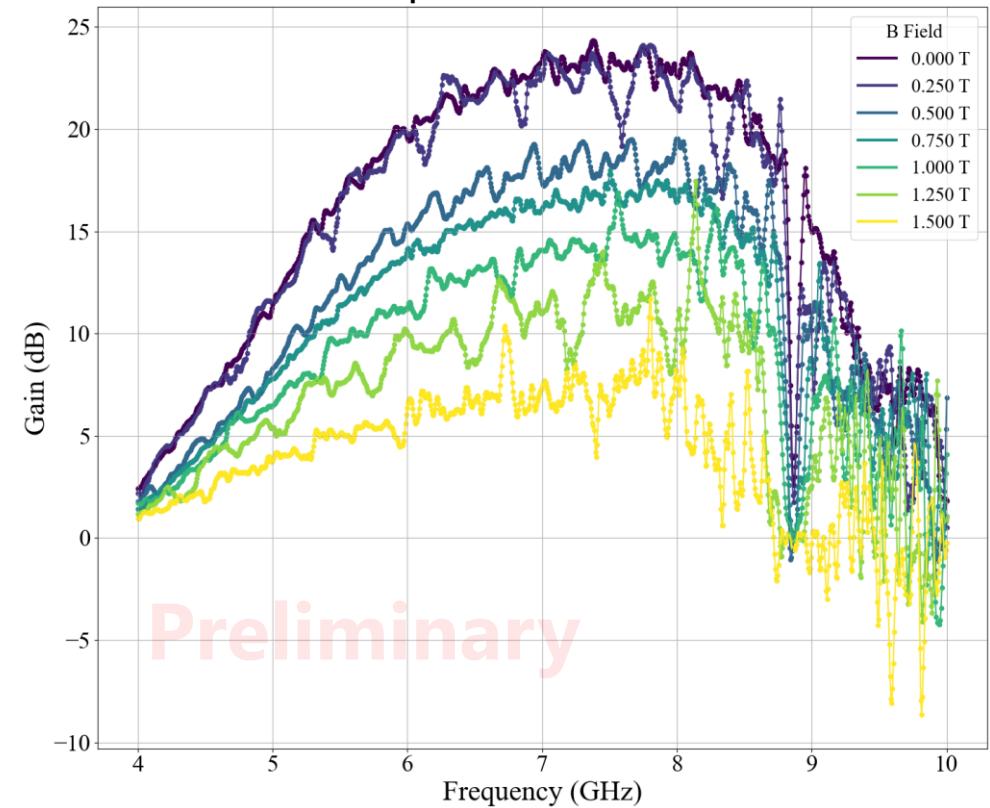
B-field perpendicular to device



Preliminary

Devices were exposed to several 2.5T magnet ramps and did not require thermal quenching to expel trapped flux

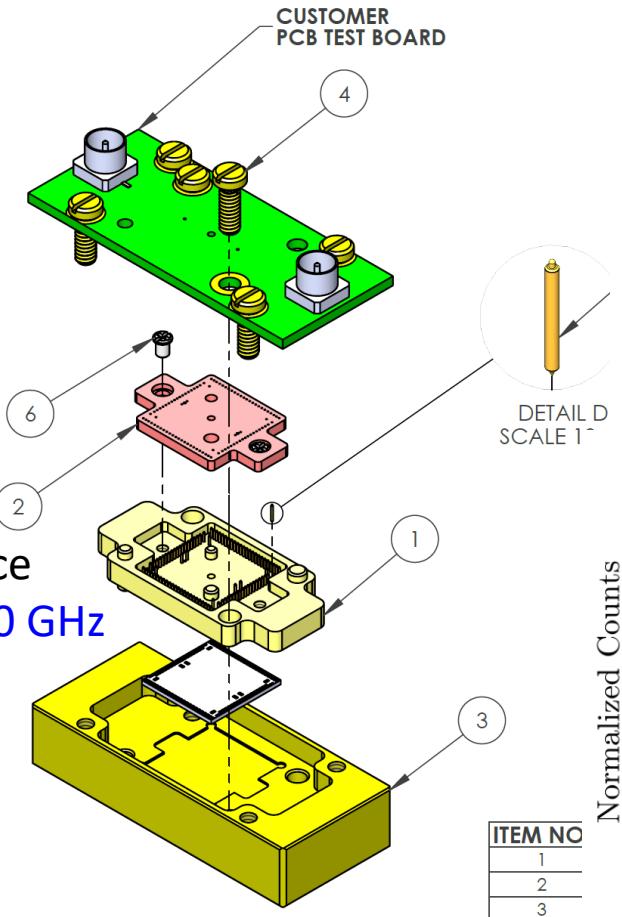
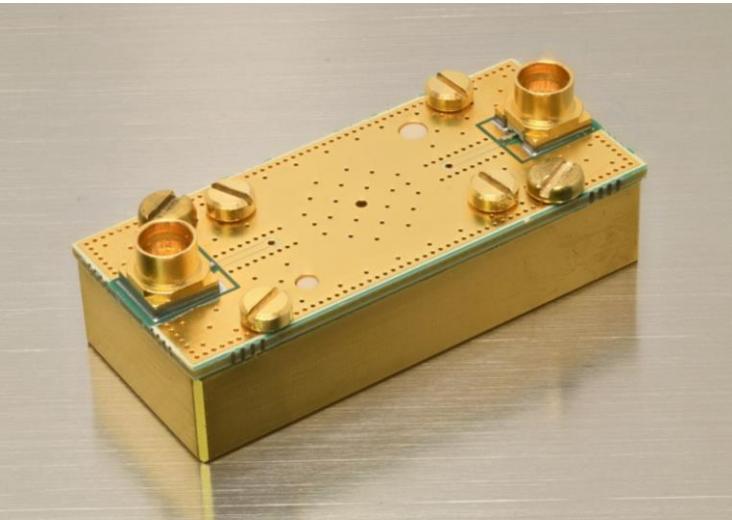
B-field parallel to device



Preliminary

KTWPA gain is maintained even with significant magnetic fields!

Improvements in packaging with Pogo pins

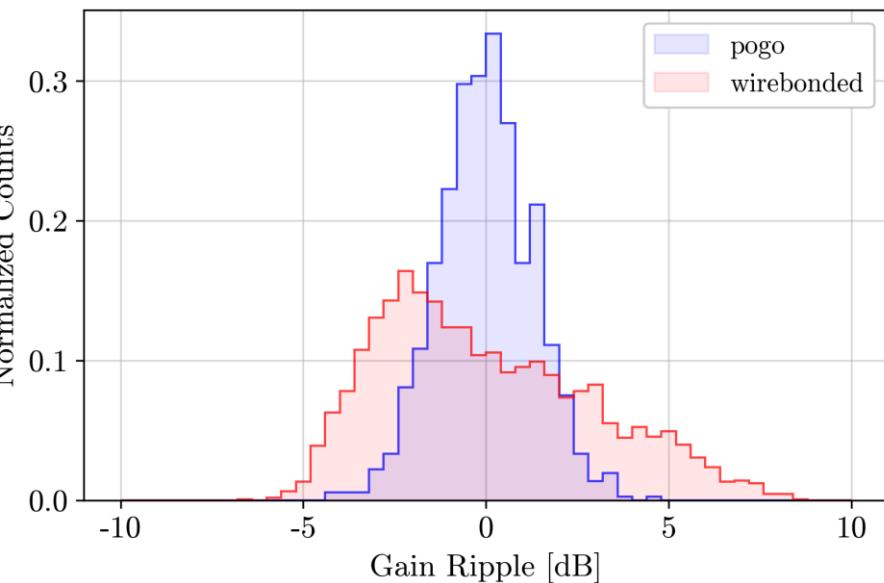
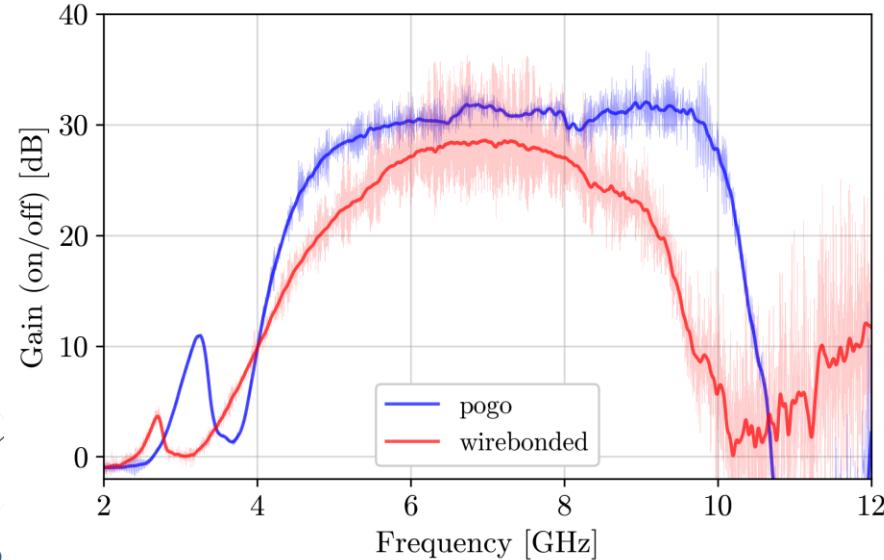


Pogo pin benefits:

- Drastic reduction of packaging inductance
- Fully optimized launch: $S_{11} < -10$ dB at 70 GHz
- Simple, repeatable assembly: <5 min

Results:

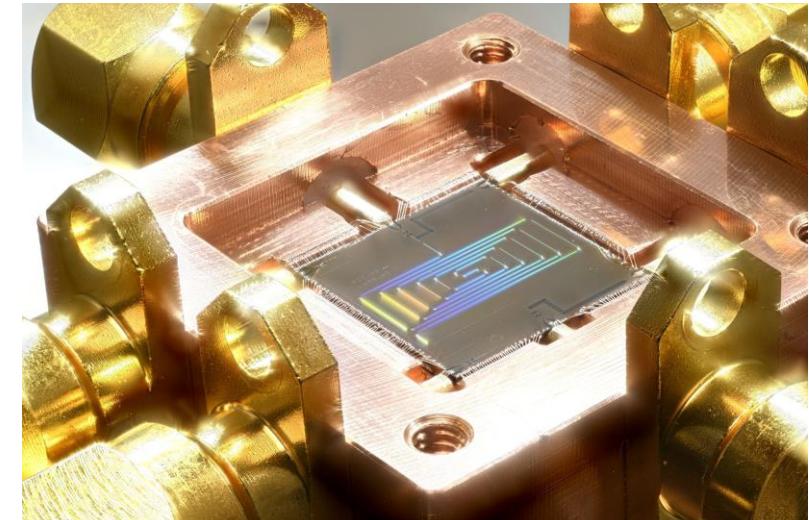
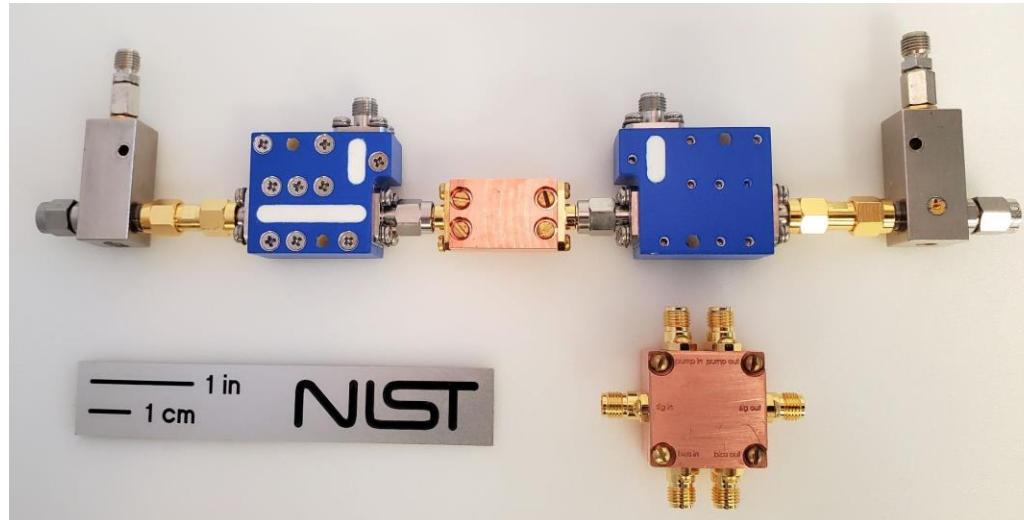
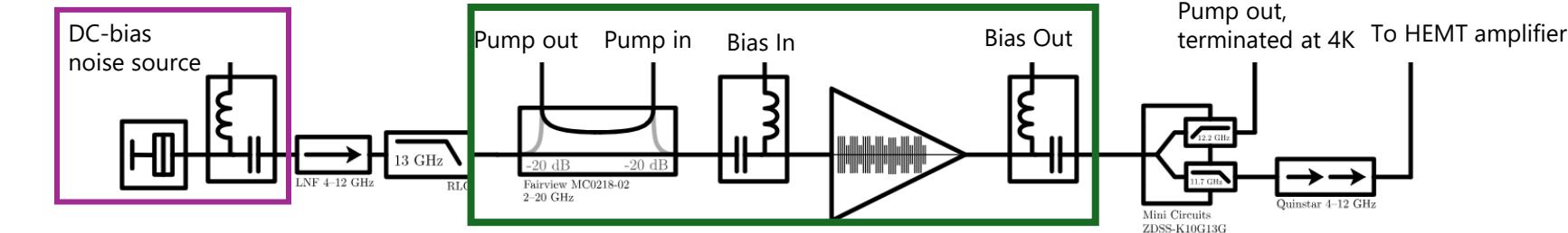
- Greater max gain, lower ripple
- Beyond-octave (4.96 GHz) bandwidth
- Operation at higher frequencies possible (future)



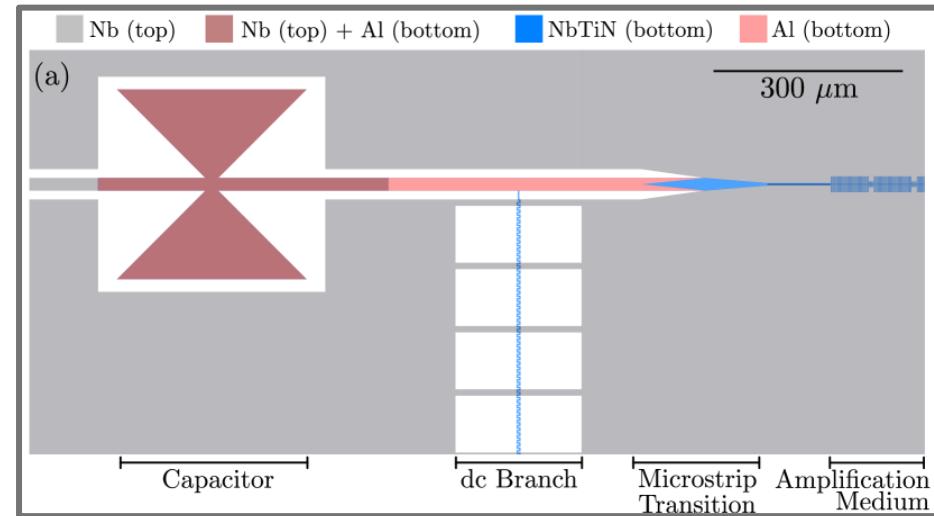
The On-chip RF Components Kit (ORCK)

- Why put things on-chip?
 - Compactify!
 - Reduce losses between signal and amplifier
 - Decrease system added noise

In V3, we have integrated all these components on chip



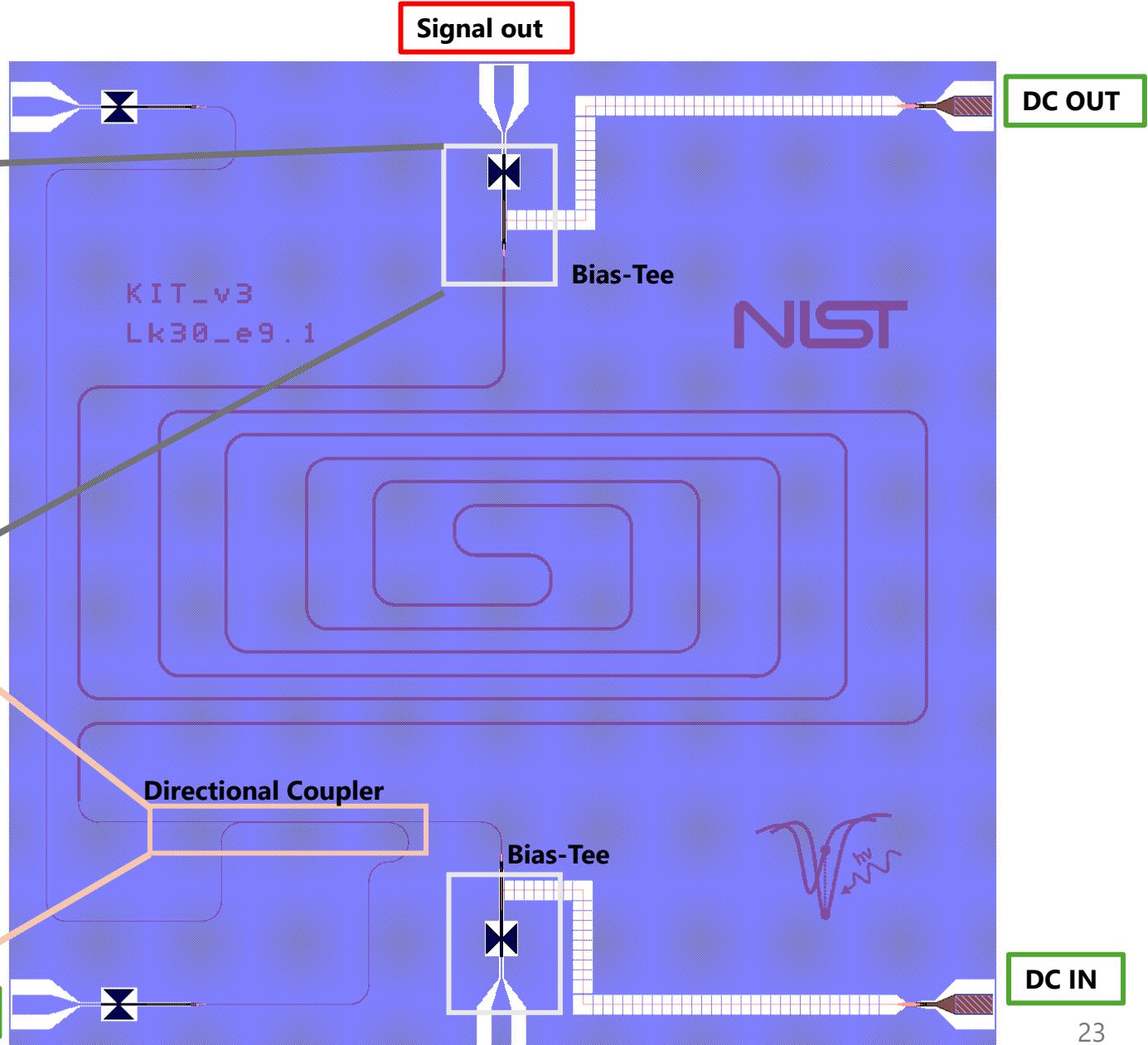
V3 ORCK device



Pump out

Signal out

DC OUT



Howe: Compact Superconducting Kinetic Inductance Traveling Wave Parametric Amplifiers with On-chip rf Components

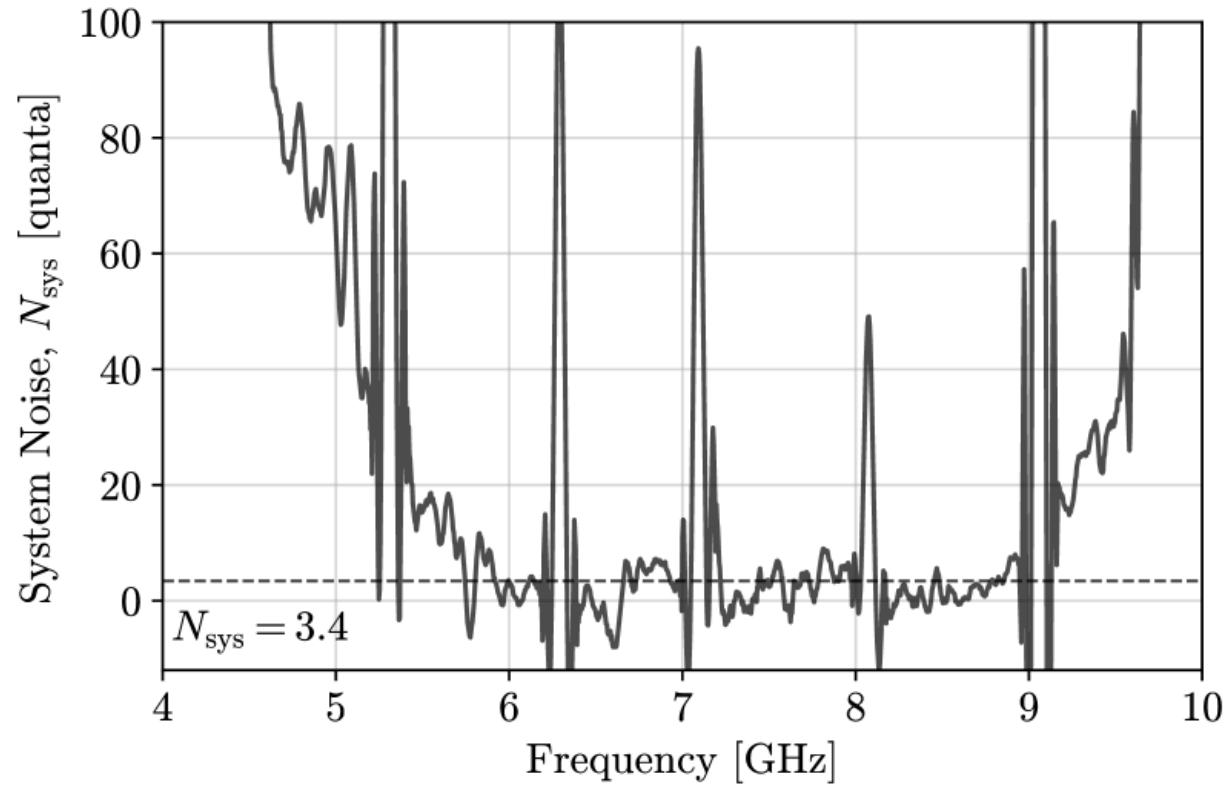
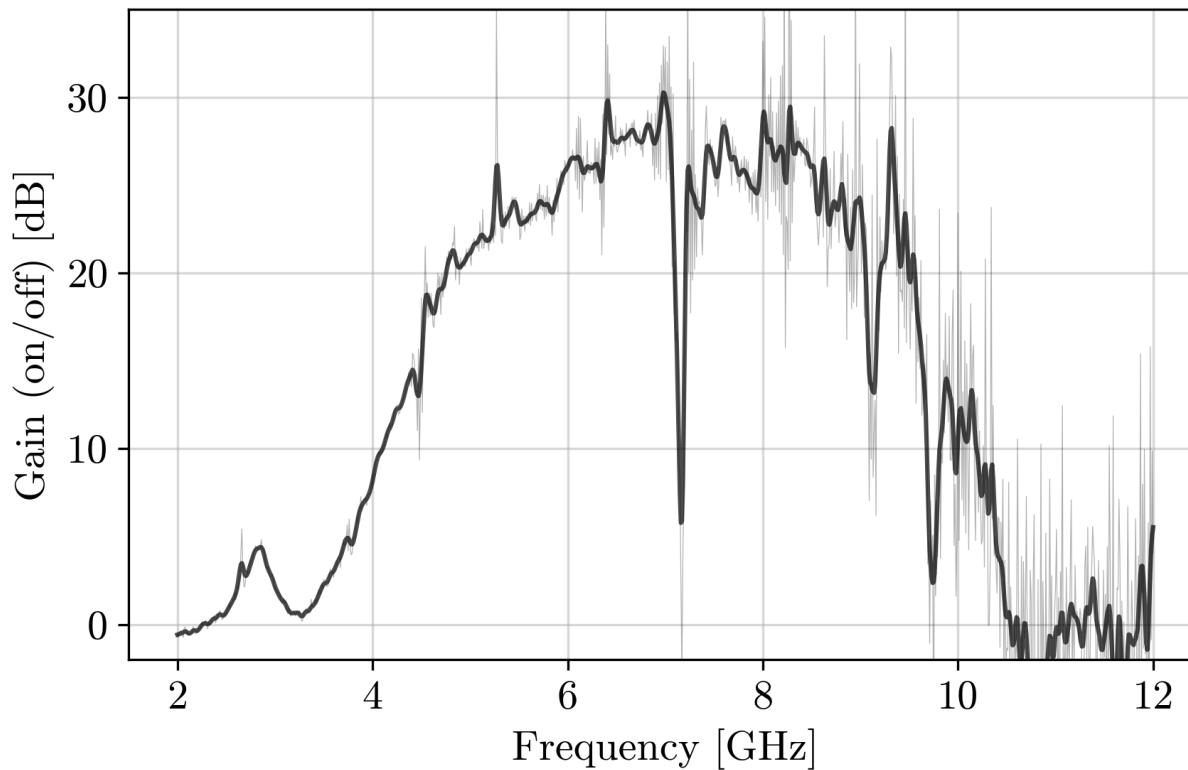
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Introduction

NIST TWPA design

Research direction

V3 ORCK device



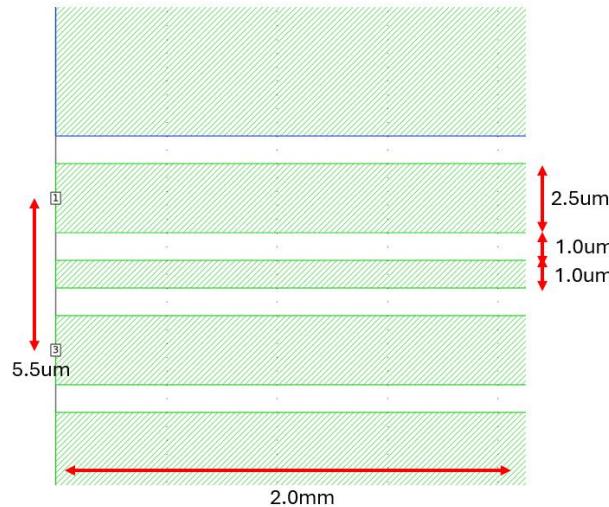
- Nearly 30dB of gain from on-chip TWPA
- Noise degraded by bias-tee inductor self resonance (~930MHz)

[Howe: Compact Superconducting Kinetic Inductance Traveling Wave Parametric Amplifiers with On-chip rf Components](#)

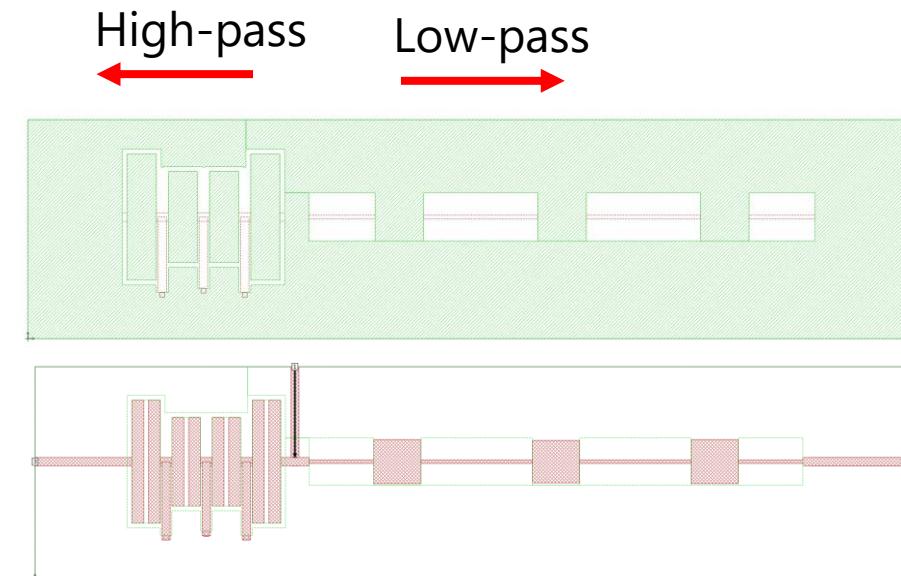
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Next generation on-chip RF components

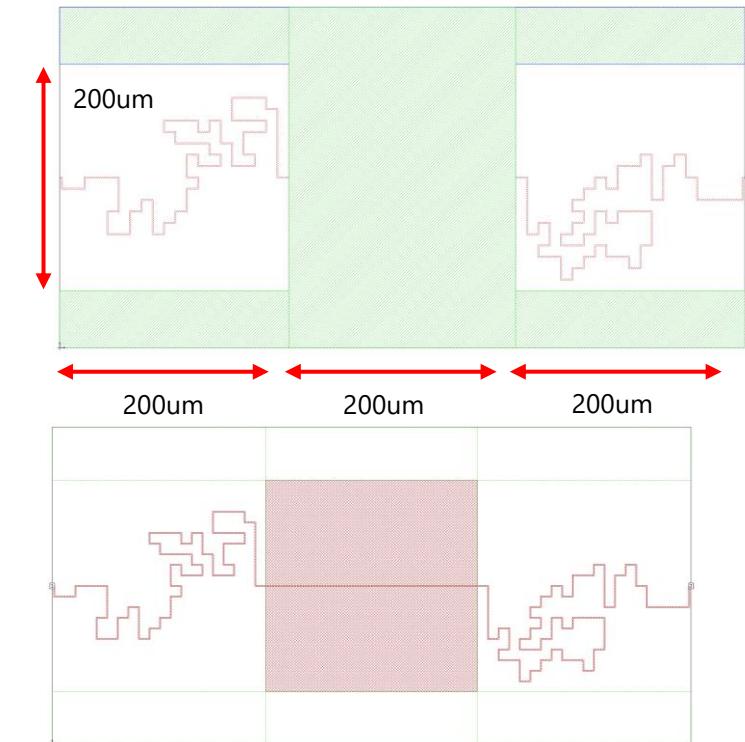
Directional coupler
for greater isolation



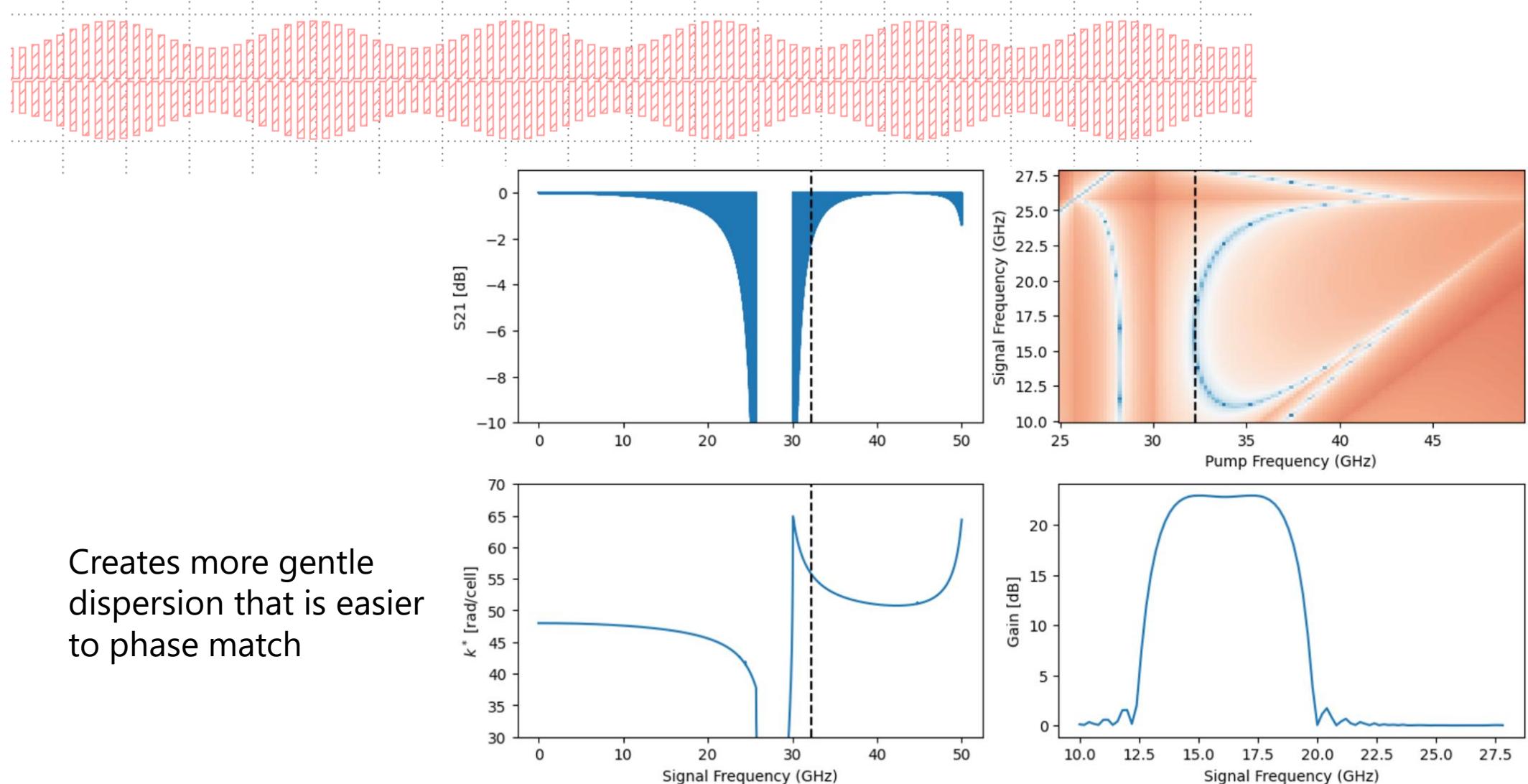
On-chip diplexers for
pulling out pump power



On-chip inductors with
exceptional self-resonance
frequencies

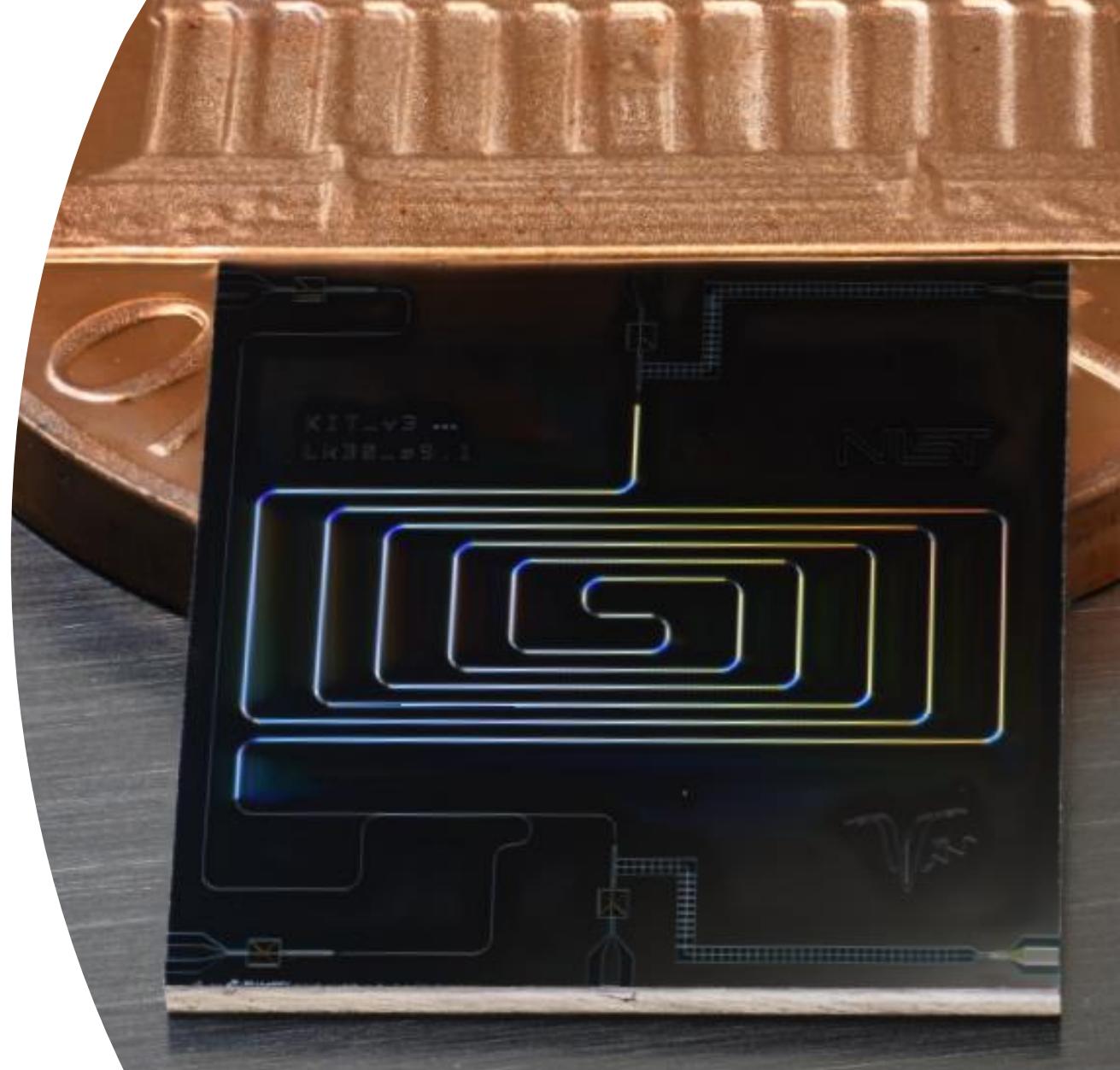


Supercell sinusoidal modulation concept



Conclusions

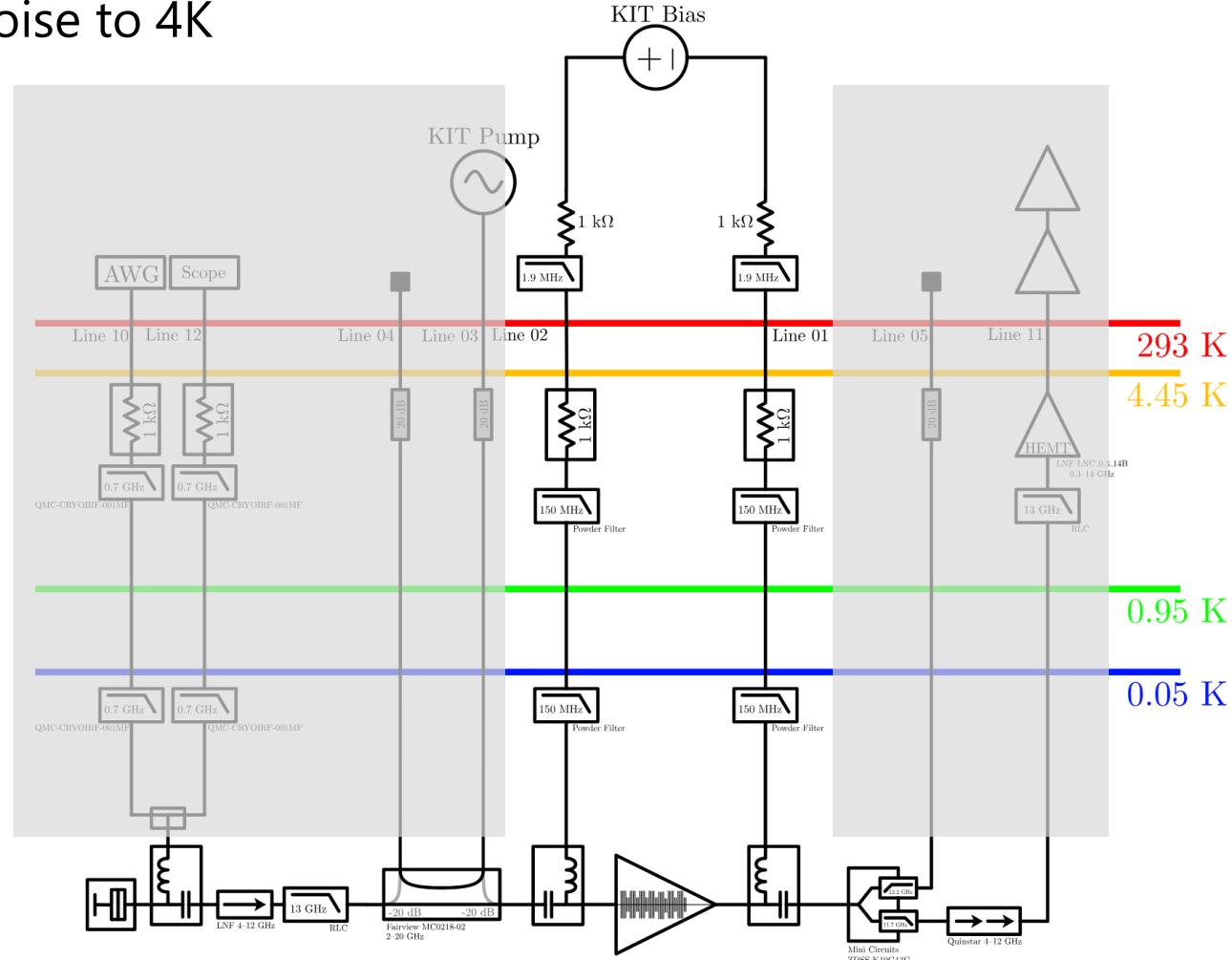
- KTWPAs are broadband, near-quantum limited devices with low sensitivity to magnetic fields
 - Well matched to the requirements for a broadband axion search
- Pushing KTWPAs to higher frequencies
 - Design and packaging
- Making improvements for the end-user of these amplifiers
 - Reducing backaction on devices
 - Reducing required pump powers



This work was supported by the U.S. Department of Energy, Office of Science, Office of High Energy Physics under Award DE-SC0026061.

Operation of a KI-TWPA

- To bring in the DC bias, we need bias tees on either side of the device
 - Each DC bias line needs some low-pass filtering and some in-line resistance to thermalize noise to 4K



Operation of a KI-TWPA

- We always want a diplexer on the output side of the amplifier to avoid saturating amplifiers further up the readout chain
- Either a diplexer or a directional coupler to bring the pump in
 - Diplexer offers higher isolation to device (finding the right combo of frequencies can be tricky), but will need an attenuator at the mK stage
 - Directional coupler thermalizes noise at mK stage is wideband

Two common examples

